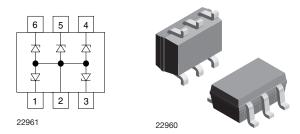
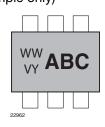


Vishay Semiconductors

Five-Line ESD Protection Diode Array in SOT-363



MARKING (example only)



Bar = cathode marking

X = date code

Y = type code (see table below)

DESIGN SUPPORT TOOLS AVAILABLE





- Compact SOT-363 package
- 5-line unidirectional ESD-protection
- Working range 5V to 26 V
- ESD immunity acc. IEC 61000-4-2 ±20kV to ± 30 kV contact discharge ±20kV to ± 30 kV air discharge
- AEC-Q101 qualified available
- Lead plating: Sn (e3)
 - soldering can be checked by standard vision inspection
 - (AOI = automated optical inspection)
- · Material categorization: for definitions of compliance please see www.vishay.com/doc?99912







RoHS HALOGEN

FREE GREEN

(5-2008)

ORDERING INFORMATION										
		ENVIRON								
PART NUMBER (EXAMPLE)	AEC-Q101 QUALIFIED	RoHS COMPLIANT + LEAD (Pb)-FREE TERMINATIONS			ORDERING CODE (EXAMPLE)					
		GREEN		MOQ = 15K/BOX						
VESD05A5-06G	-	G	3	-08	VESD05A5-06G-G3-08					
VESD05A5-06G	Н	G	3	-08	VESD05A5-06GHG3-08					

PACKAGE DATA										
DEVICE NAME	PACKAGE NAME	TYPE CODE	WEIGHT	MOLDING COMPOUND FLAMMABILITY RATING	MOISTURE SENSITIVITY LEVEL	SOLDERING CONDITIONS				
VESD05A5-06G		D05				Peak temperature				
VESD12A5-06G	SOT-363	D12	7 00 ma	UL 94 V-0	MSL level 1					
VESD16A5-06G	501-303	D16	7.22 mg	OL 94 V-0	(according J-STD-020)	max. 260°C				
VESD26A5-06G		D26								



ABSOLUTE MAXIMUM RATINGS VESD05A5-06G									
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT					
Peak pulse current	Acc. IEC 61000-4-5, 8/20 μs/single shot	I _{PPM}	8.7	Α					
Peak pulse power	Acc. IEC 61000-4-5, 8/20 µs/single shot	P _{PP}	100	W					
ECD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	W	30	kV					
ESD immunity	Air discharge acc. IEC 61000-4-2; 10 pulses	V_{ESD}	30	kV					
Operating temperature	Junction temperature	TJ	-55 to +150	°C					
Storage temperature		T _{stg}	-55 to +150	°C					

ABSOLUTE MAXIMUM	ABSOLUTE MAXIMUM RATINGS VESD12A5-06G								
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT					
Peak pulse current	Acc. IEC 61000-4-5, 8/20 μs/single shot	I _{PPM}	4.4	Α					
Peak pulse power	Acc. IEC 61000-4-5, 8/20 μs/single shot	P _{PP}	100	W					
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	W	30	kV					
L3D initiality	Air discharge acc. IEC 61000-4-2; 10 pulses	V _{ESD}	30	kV					
Operating temperature	Junction temperature	T _J	-55 to +150	°C					
Storage temperature		T _{stg}	-55 to +150	°C					

ABSOLUTE MAXIMUM RATINGS VESD16A5-06G									
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT					
Peak pulse current	Acc. IEC 61000-4-5, 8/20 μs/single shot	I _{PPM}	3.6	Α					
Peak pulse power	Acc. IEC 61000-4-5, 8/20 μs/single shot	P _{PP}	100	W					
CCD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	\/	30	kV					
ESD immunity	Air discharge acc. IEC 61000-4-2; 10 pulses	V_{ESD}	30	kV					
Operating temperature	Junction temperature	T _J	-55 to +150	°C					
Storage temperature		T _{stg}	-55 to +150	°C					

ABSOLUTE MAXIMUM RATINGS VESD26A5-06G									
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT					
Peak pulse current	Acc. IEC 61000-4-5, 8/20 μs/single shot	I _{PPM}	2.1	Α					
Peak pulse power	Acc. IEC 61000-4-5, 8/20 μs/single shot	P _{PP}	100	W					
ECD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	W	20	kV					
ESD immunity	Air discharge acc. IEC 61000-4-2; 10 pulses	V _{ESD}	20	kV					
Operating temperature	Junction temperature	T_J	-55 to +150	°C					
Storage temperature		T _{stg}	-55 to +150	°C					



ELECTRICAL CHARACTERISTICS VESD05A5-06G (T _{amb} = 25 °C, unless otherwise specified)									
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT			
Protection paths	Number of lines which can be protected	N _{channel}	-	-	1	lines			
Reverse stand off voltage	Max. reverse working voltage	V_{RWM}	-	-	5	V			
Reverse voltage	at I _R = 1 μA	V_R	5	-	-	V			
Reverse current	at V _R = 5 V	I _R	-	0.01	0.1	μA			
Reverse breakdown voltage	at I _R = 1 mA	V_{BR}	6.85	7.26	7.65	V			
Reverse clamping voltage	at $I_{PP} = I_{PPM} = 8.7 \text{ A}$, $t_p = 8/20 \mu\text{s}$	V _C	-	10.3	11.5	V			
Forward clamping voltage	at $I_{PP} = 1 \text{ A}$, $t_p = 300 \mu\text{s}$	V_{F}	0.9	1.1	1.2	V			
Torward clamping voltage	at $I_{PP} = I_{PPM} = 8.7 \text{ A}$, $t_p = 8/20 \mu\text{s}$	V_{F}	-	2.2	2.74	V			
Dynamic resistance	$t_p = 100 \text{ ns (TLP; pin 2-1)}$	r _{dyn}	-	0.2	-	Ω			
Capacitance	at $V_R = 0 V$; $f = 1 MHz$	C _D	53	67	81	pF			

ELECTRICAL CHARACTERISTICS VESD12A5-06G (T _{amb} = 25 °C, unless otherwise specified)									
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT			
Protection paths	Number of lines which can be protected	N _{channel}	-	-	1	lines			
Reverse stand off voltage	Max. reverse working voltage	V_{RWM}	-	-	12	V			
Reverse voltage	at I _R = 0.1 μA	V_R	12	-	-	V			
Reverse current	at V _R = 12 V	I _R	-	0.01	0.1	μΑ			
Reverse breakdown voltage	at I _R = 1 mA	V_{BR}	13.9	14.7	15.5	V			
Reverse clamping voltage	at $I_{PP} = I_{PPM} = 4.4 \text{ A}$, $t_p = 8/20 \mu\text{s}$	V _C	-	20.5	22.7	V			
Famus rd alamaning valtage	at $I_{PP} = 1 \text{ A}$, $t_p = 300 \mu\text{s}$	V_{F}	0.9	1.1	1.2	V			
Forward clamping voltage	at $I_{PP} = I_{PPM} = 4.4 \text{ A}, t_p = 8/20 \mu\text{s}$	V _F	-	1.6	1.88	V			
Dynamic resistance	t _p = 100 ns (TLP); pin 2-1	r _{dyn}	-	0.4	-	Ω			
Capacitance	at V _R = 0 V; f = 1 MHz	C _D	26	33	40	pF			

ELECTRICAL CHARACTERISTICS VESD16A5-06G (T _{amb} = 25 °C, unless otherwise specified)									
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT			
Protection paths	Number of lines which can be protected	N _{channel}	-	-	1	lines			
Reverse stand off voltage	Max. reverse working voltage	V_{RWM}	-	-	16	V			
Reverse voltage	at I _R = 0.1 μA	V_R	16	-	-	V			
Reverse current	at V _R = 16 V	I _R	-	0.01	0.1	μΑ			
Reverse breakdown voltage	at I _R = 1 mA	V_{BR}	17	17.9	18.8	V			
Reverse clamping voltage	at $I_{PP} = I_{PPM} = 3.6 \text{ A}, t_p = 8/20 \mu\text{s}$	V _C	-	25.3	28	V			
Commend alamanian maltana	at I _{PP} = 1 A, t _p = 300 μs	V _F	0.9	1.1	1.2	V			
Forward clamping voltage	at I _{PP} = I _{PPM} = 3.6 A, t _p = 8/20 μs	V_{F}	-	1.5	1.72	V			
Dynamic resistance	t _p = 100 ns (TLP); pin 2-1	r _{dyn}	-	0.53	-	Ω			
Capacitance	at V _R = 0 V; f = 1 MHz	C_D	21	27	33	pF			





ELECTRICAL CHARACTERISTICS VESD26A5-06G (T _{amb} = 25 °C, unless otherwise specified)									
PARAMETER	TEST CONDITIONS/REMARKS	DITIONS/REMARKS SYMBOL MIN. TYP. MAX. UI							
Protection paths	Number of lines which can be protected	N _{channel}	-	-	1	lines			
Reverse stand off voltage	Max. reverse working voltage	V_{RWM}	-	-	26	V			
Reverse voltage	at I _R = 0.1 μA	V_R	26	-	-	V			
Reverse current	at V _R = 26 V	I _R	-	< 0.01	0.1	μΑ			
Reverse breakdown voltage	at I _R = 1 mA	V_{BR}	27.6	29.1	30.6	V			
Reverse clamping voltage	at I _{PP} = I _{PPM} = 2.1 A, t _p = 8/20 μs	V _C	-	43	48	V			
Famuurd alamaning valtage	at $I_{PP} = 1 \text{ A}$, $t_p = 300 \mu\text{s}$	V_{F}	0.9	1.1	1.2	V			
Forward clamping voltage	at I _{PP} = I _{PPM} = 2.1 A, t _p = 8/20 μs	V_{F}	-	1.3	1.42	V			
Dynamic resistance	t _p = 100 ns (TLP); pin 2-1	r _{dyn}	-	1.9	-	Ω			
Capacitance	at V _R = 0 V; f = 1 MHz	C _D	14	17.5	21	pF			

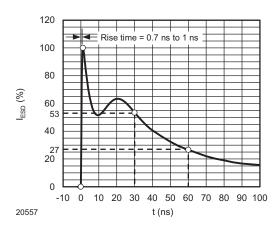


Fig. 1 - ESD Discharge Current Wave Form acc. IEC 61000-4-2 (330 Ω / 150 pF)

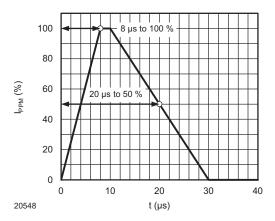


Fig. 2 - 8/20 µs Peak Pulse Current Wave Form acc. IEC 61000-4-5

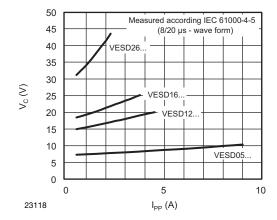


Fig. 3 - Typical Peak Clamping Voltage vs. Peak Pulse Current

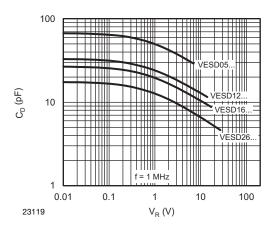


Fig. 4 - Typical Capacitance vs. Reverse Voltage

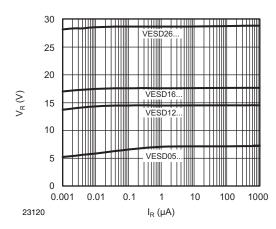


Fig. 5 - Typical Reverse Voltage vs. Reverse Current

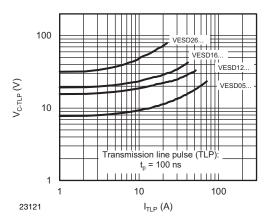
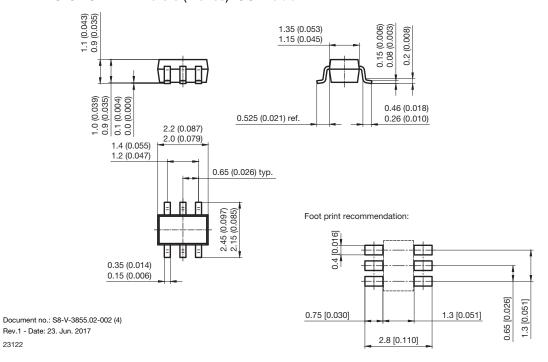


Fig. 6 - Typical Clamping Voltage vs. Peak Pulse Current

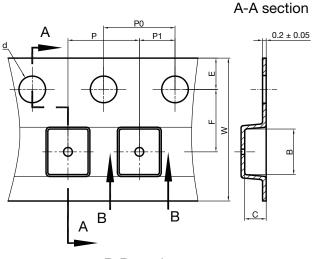
Vishay Semiconductors

PACKAGE DIMENSIONS in millimeters (Inches): SOT-363



CARRIER TAPE SOT-363

23122



B-B section



Cummulative tolerances of 10 sprocket holes is \pm 0.2 mm

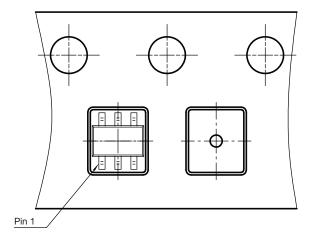
Dimensions in millimeters										
Packaging type	Α	В	С	d	Е	F	P0	Р	P1	W
SOT-363	2.25	2.55	1.20	Ø 1.5	1.75	3.50	4.00	4.00	2.00	8.00
(Tolerance)	± 0.1	± 0.1	± 0.1	+0.1/-0	± 0.1	± 0.1	± 0.05	± 0.1	± 0.05	+0.3/-0.1

Document no. S8-V-3855.02-003 (4) Created - Date: 25. April. 2017 22968



Vishay Semiconductors

ORIENTATION IN CARRIER TAPE SOT-363



Document no. S8-V-3855.02-004 (4) Created - Date: 25. April 2017



Vishay

Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.

单击下面可查看定价,库存,交付和生命周期等信息

>>Vishay(威世)